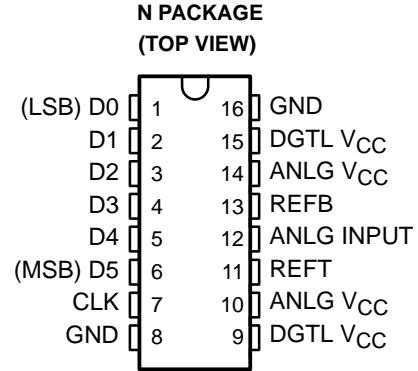


# TL5501 6-BIT ANALOG-TO-DIGITAL CONVERTER

SLAS026 – OCTOBER 1989 – REVISED APRIL 1990

- **6-Bit Resolution**
- **Linearity Error . . .  $\pm 0.8\%$**
- **Maximum Conversion Rate . . . 30 MHz Typ**
- **Analog Input Voltage Range**  
 $V_{CC}$  to  $V_{CC} - 2 V$
- **Analog Input Dynamic Range . . . 1 V**
- **TTL Digital I/O Level**
- **Low Power Consumption**  
200 mW Typ
- **5-V Single-Supply Operation**
- **Interchangeable With Fujitsu MB40576**

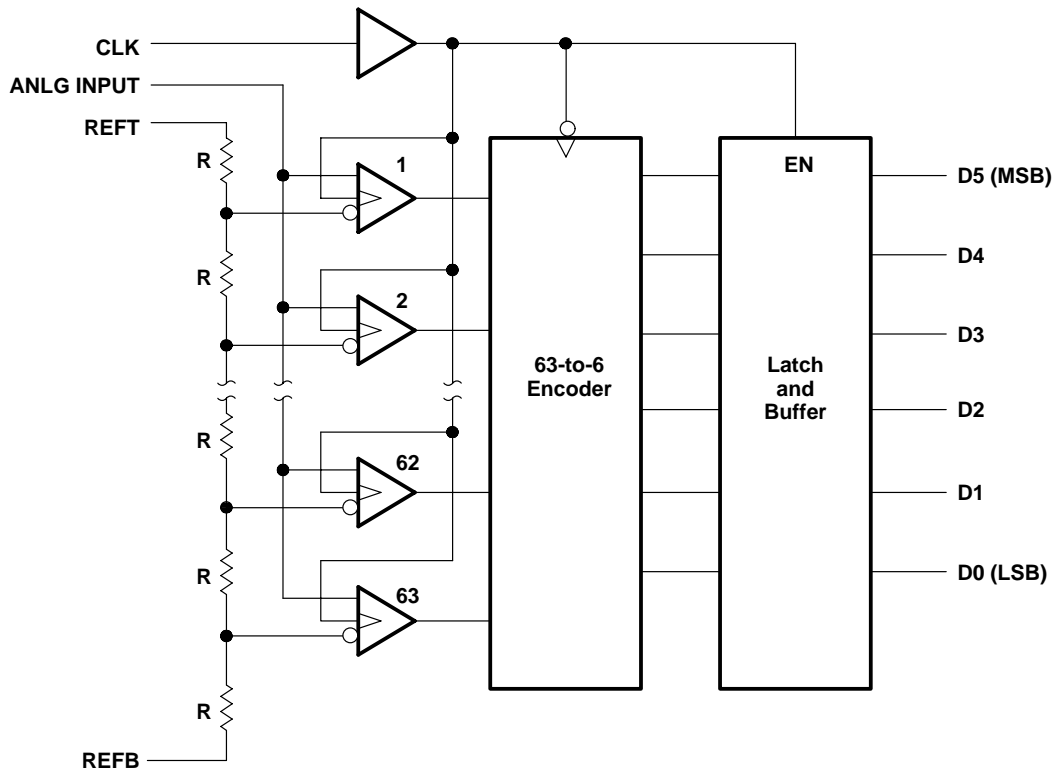


## description

The TL5501 is a low-power ultra-high-speed video-band analog-to-digital converter that uses the Advanced Low-Power Schottky (ALS) process. It utilizes the full-parallel comparison (flash method) for high-speed conversion. It converts wide-band analog signals (such as a video signal) to a digital signal at a sampling rate of dc to 30 MHz. Because of this high-speed capability, the TL5501 is suitable for digital video applications such as digital TV, video processing with a computer, or radar signal processing.

The TL5501 is characterized for operation from 0°C to 70°C.

## functional block diagram



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS  
INSTRUMENTS**

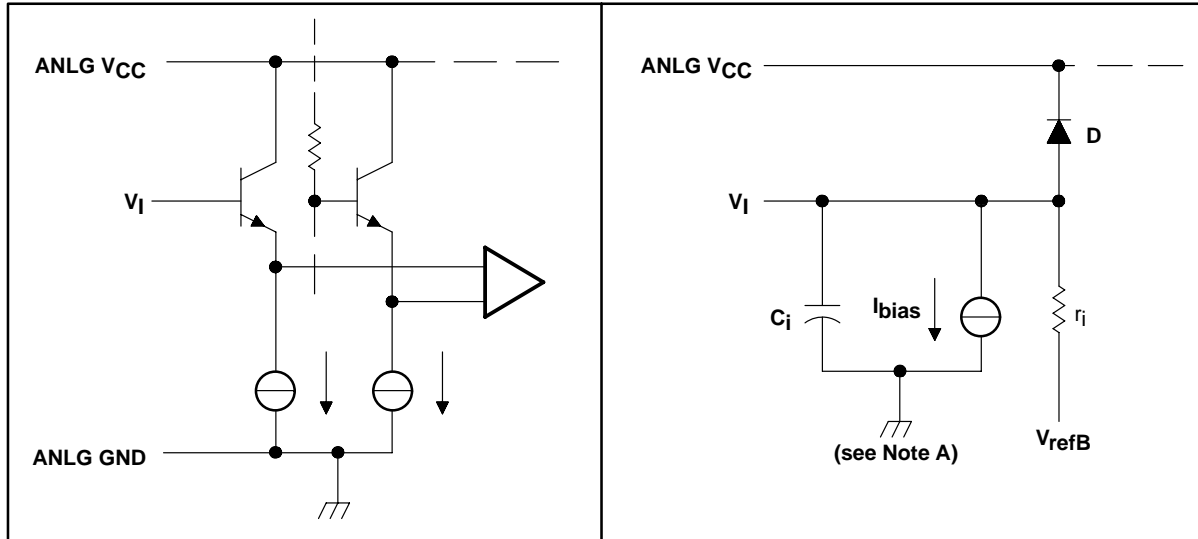
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# TL5501 6-BIT ANALOG-TO-DIGITAL CONVERTER

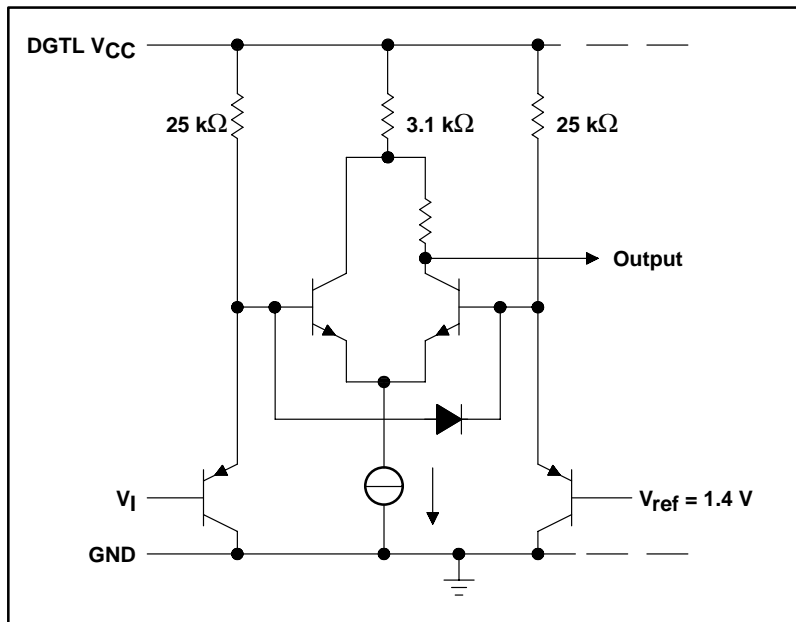
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## equivalents of analog input circuit



NOTE A:  $C_i$  – nonlinear emitter-follower junction capacitance  
 $r_i$  – linear resistance model for input current transition caused by comparator switching.  
 $V_I < V_{refB}$ : Infinite; CLK high: infinite.  
 $V_{refB}$  – voltage at REFB terminal  
 $I_{bias}$  – constant input bias current  
 $D$  – base-collector junction diode of emitter-follower transistor

## equivalent of digital input circuit



**FUNCTION TABLE**

STEP	ANALOG INPUT VOLTAGE	DIGITAL OUTPUT CODE					
0	3.992 V	L	L	L	L	L	L
1	4.008 V	L	L	L	L	L	H
31	4.488 V	L	H	H	H	H	H
32	4.508 V	H	L	L	L	L	L
33	4.520 V	H	L	L	L	L	H
62	4.984 V	H	H	H	H	H	L
63	5.000 V	H	H	H	H	H	H

† These values are based on the assumption that  $V_{refB}$  and  $V_{refT}$  have been adjusted so that the voltage at the transition from digital 0 to 1 ( $V_{ZT}$ ) is 4.000 V and the transition to full scale ( $V_{FT}$ ) is 4.992 V. 1 LSB = 16 mV.

**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)**

- Supply voltage range, ANLG  $V_{CC}$  (see Note 1) ..... –0.5 V to 7 V
- Supply voltage range, DGTL  $V_{CC}$  ..... –0.5 V to 7 V
- Input voltage range at digital input,  $V_I$  ..... –0.5 V to 7 V
- Input voltage range at analog input,  $V_I$  ..... –0.5 V to ANLG  $V_{CC}$  +0.5 V
- Analog reference voltage range,  $V_{ref}$  ..... –0.5 V to ANLG  $V_{CC}$  +0.5 V
- Storage temperature range ..... –55°C to 150°C
- Operating free-air temperature range ..... 0°C to 70°C
- Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds ..... 260°C

NOTE 1: All voltage values are with respect to the network ground terminal.

**recommended operating conditions**

	MIN	NOM	MAX	UNIT
Supply voltage, ANLG $V_{CC}$	4.75	5	5.25	V
Supply voltage, DGTL $V_{CC}$	4.75	5	5.25	V
High-level input voltage, $V_{IH}$	2			V
Low-level input voltage, $V_{IL}$			0.8	V
Input voltage at analog input, $V_I$ (see Note 2)	4		5	V
Analog reference voltage (top side), $V_{refT}$ (see Note 2)	4	5	5.1	V
Analog reference voltage (bottom side), $V_{refB}$ (see Note 2)	3	4	4.1	V
High-level output current, $I_{OH}$	–400			μA
Low-level output current, $I_{OL}$			4	mA
Clock pulse duration, high-level or low-level, $t_w$	25			ns
Operating free-air temperature, $T_A$	0		70	°C

NOTE 2:  $V_{refB} < V_I < V_{refT}$ ;  $V_{refT} - V_{refB} = 1 \text{ V} \pm 0.1 \text{ V}$ .

# TL5501 6-BIT ANALOG-TO-DIGITAL CONVERTER

SLAS026 – OCTOBER 1989 – REVISED APRIL 1990

## electrical characteristics over operating supply voltage range, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

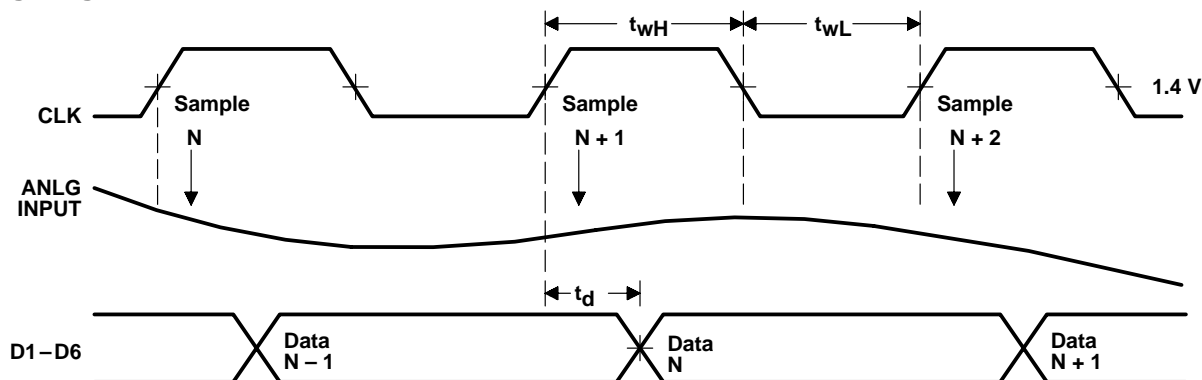
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_I$ Analog input current	$V_I = 5\text{ V}$			75	$\mu\text{A}$
	$V_I = 4\text{ V}$			73	
$I_{IH}$ Digital high-level input current	$V_I = 2.7\text{ V}$		0	20	$\mu\text{A}$
$I_{IL}$ Digital low-level input current	$V_I = 0.4\text{ V}$	-400	-40		$\mu\text{A}$
$I_I$ Digital input current	$V_I = 7\text{ V}$			100	$\mu\text{A}$
$I_{refB}$ Reference current	$V_{IrefB} = 4\text{ V}$		-4	-7.2	mA
$I_{refT}$ Reference current	$V_{IrefB} = 5\text{ V}$		4	7.2	mA
$V_{OH}$ High-level output voltage	$I_{OH} = -400\ \mu\text{A}$	2.7			V
$V_{OL}$ Low-level output voltage	$I_{OL} = 1.6\text{ mA}$			0.4	V
$r_i$ Analog input resistance		100			$\text{k}\Omega$
$1C_i$ Analog input capacitance			35	65	pF
$I_{CC}$ Supply current			40	60	mA

## operating characteristics over operating supply voltage range, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
$E_L$ Linearity error				$\pm 0.8$	%FSR
$f_{max}$ Maximum conversion rate		20	30		MHz
$t_d$ Digital output delay time	See Figure 3		15	30	ns

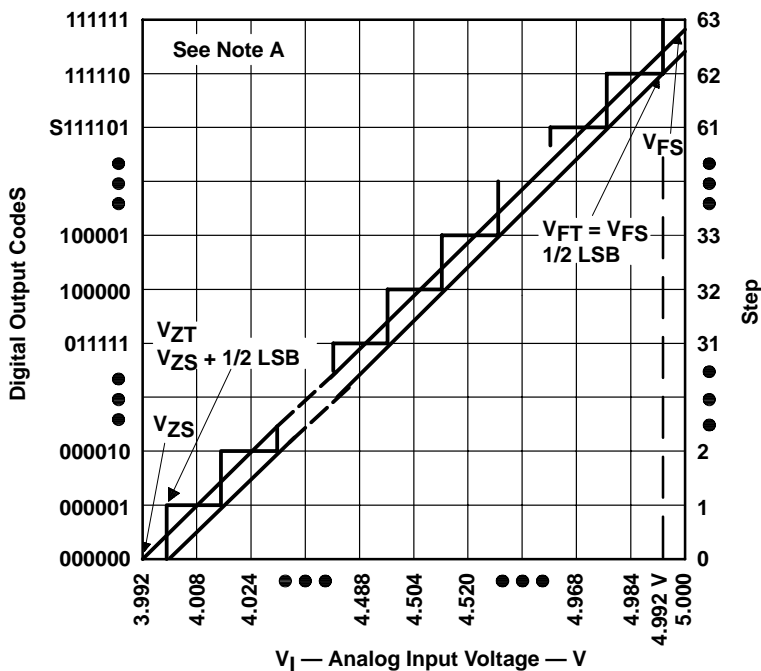
† All typical values are at  $V_{CC} = 5\text{ V}$ ,  $V_{ref} = 4\text{ V}$ ,  $T_A = 25^\circ\text{C}$ .

## timing diagram



TYPICAL CHARACTERISTICS

IDEAL CONVERSION CHARACTERISTICS



NOTE A: This curve is based on the assumption that  $V_{refB}$  and  $V_{refT}$  have been adjusted so that the voltage at the transition from digital 0 to 1 ( $V_{ZT}$ ) is 4.000 V and the transition to full scale ( $V_{FT}$ ) is 4.992 V. 1 LSB = 16 mV.

Figure 1

END-POINT LINEARITY ERROR

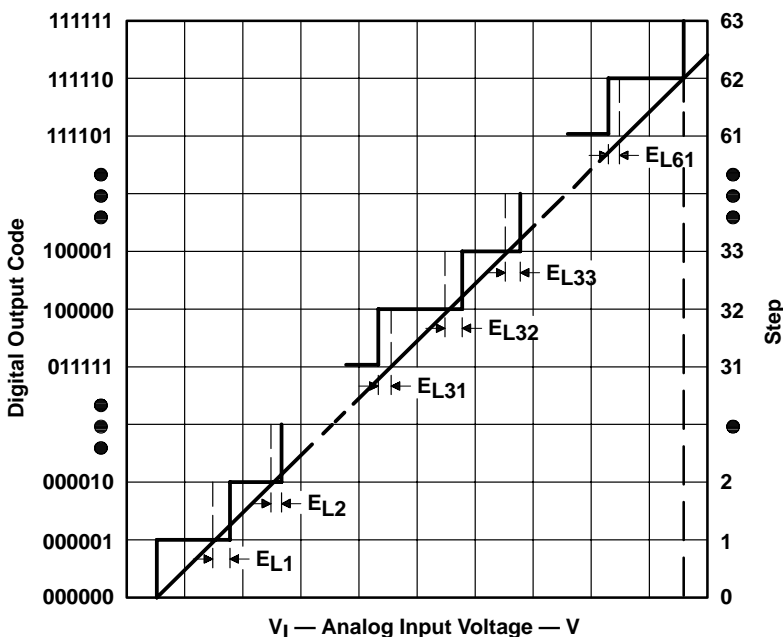


Figure 2

# TL5501 6-BIT ANALOG-TO-DIGITAL CONVERTER

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## PARAMETER MEASUREMENT INFORMATION

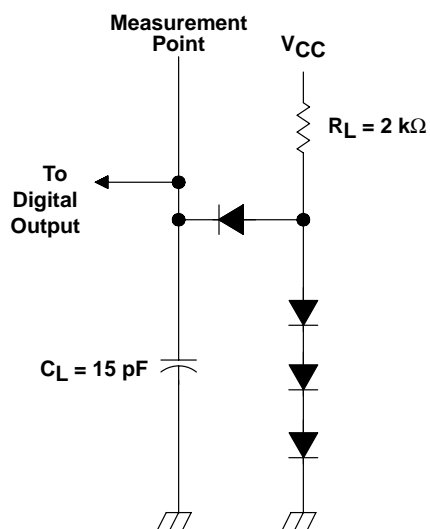


Figure 3. Load Circuit

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